Docket No.: M4065.0694/P694-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
John T. Moore et al.

Application No.: Not Yet Assigned

Filed: February 13, 2004 Art Unit: N/A

For: METHODS OF FORMING NON-VOLATILE RESISTANCE VARIABLE DEVICES, AND NON-VOLATILE RESISTANCE VARIABLE DEVICES

Examiner: Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT (IDS)

MS Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement accompanies the new patent application submitted herewith.

Copies of the references on the PTO/SB/08 are not provided.

Those patent(s) or publication(s) which are marked with a double asterisk (**) next to the Cite No. in the attached form PTO/SB/08 (facsimile) are not supplied

because they were previously cited by or submitted to the Office in a prior application number 09/999,883, filed October 31, 2001 and relied upon in this application for an earlier filing date under 35 U.S.C. 120.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0694/P694-A. A duplicate copy of this paper is enclosed.

Dated: February 13, 2004

Respectfully submitted,

By_____

Thomas J. D'Amico
Registration No.: 28,371
DICKSTEIN SHAPIRO MORIN &
OSHINSKY LLP
2101 L Street NW
Washington, DC 20037-1526
(202) 785-9700
Attorney for Applicant

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Sheet 1 of 8

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U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Initials*	Cite No.[1]	Foreign Patent Document Country Code[3]-Number[4]-Kind Code[5] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
	BA	WO 97/48032	12/18/1997	Kozicki et al. **		
	BB	WO 99/28914	06/10/1999	Kozicki et al. **		

Examiner Signature		Date Considered	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

[1] Applicant's unique citation designation number (optional). [2] See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. [3] Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4] For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. [5] Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6] Applicant is to place a check mark here if English language Translation is attached.

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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Sheet 6 | | 8

Complete if Known	
Application Number	Not Yet Assigned
Filing Date	February 13, 2004
First Named Inventor	John T. Moore
Group Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0694/P694-A

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Group Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
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	AC	09/943,190		Campbell, et al.			08/29/01
	AD	09/943,199		Campbell, et al.			08/29/01
	AE	09/943,187		Campbell, et al.			08/29/01
	AF	5,238,862	08/24/93	Blalock et al.	437	52	
	AG	5,360,981	11/01/94	Owen et al.	257	4	
	AH	5,761,115	06/02/98	Kozicki et al.	365	182	
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	AB	3,743,847	07/03/73	Boland	250	510	
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	AO		Miyatani, *Electrical Porperties of Ag_2Se*, 13 J. Phys. Soc. Japan, p. 317 (1958).
	AP		Mizusaki et al. *Kinetic Studies on the Selenization of Silver*, 47 BUL. CHEM. SOC. JAPAN,, No. 11
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Form PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)	ATTY. DOCKET NO. MI22-1850	SERIAL NO. 09/999,883
	APPLICANT: John T. Moore et al.	
	FILING DATE October 31, 2001	GROUP 2813

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	AA	10/077,867		Campbell et al. (as filed)			02/20/2002
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	AC	4,405,710	09/20/83	Balasubramanyam et al.	430	311	
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	AE	4,499,557	02/12/85	Holmberg et al.	365	163	
	AF	5,315,131	05/24/94	Kishimoto et al.	257	57	
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	AM	00/48196 A1	17.08.00	WIPO (Kozicki et al.)				
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